## NSN 5961-01-442-1999

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Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-442-1999 **Inclosure Material:** Ceramic **Overall Length:** 0.785 inches **Terminal Length:** 0.120 inches **Overall Height:** 0.280 inches **Overall Width:** 0.300 inches **End Application:** Signal generator **Mounting Facility Quantity:** 14 **Component Name And Quantity:** 4 semiconductor device diode **Mounting Method: Terminal Semiconductor Material:** Silicon all semiconductor Voltage Rating In Volts Per Characteristic: 60.0 breakdown voltage, collector-to-emitter, base open all semiconductor and 40.0 working peak off-state voltage all semiconductor **Current Rating Per Characteristic:** 0.50 milliamperes source cutoff current of standard range all semiconductor **Power Rating Per Characteristic:** 1900.0 milliwatts small-signal input power, common-emitter absolute all semiconductor **Maximum Operating Tempurature Per Measurement Point:** -65.0 degrees celsius case and 175.0 degrees celsius case **Special Features:** 19 mm lg., 6.3 mm w., 5.0 mm h. **Terminal Type And Quantity:** 14 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:**